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Kind regards,

Team Nexperia



2N7002PT

60 V, 310 mA N-channel Trench MOSFET Rev. 1 — 2 July 2010

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT416 (SC-75) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] _	-	310	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	-3	
3	D	drain	1 2	G

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
2N7002PT	SC-75	plastic surface-mounted package; 3 leads	SOT416	

4. Marking

Table 4. Marking codes

Type number	Marking code
2N7002PT	Z1

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

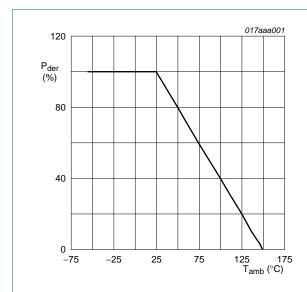
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	V _{GS} = 10 V	<u>[1]</u>		
		T _{amb} = 25 °C	-	310	mA
		T _{amb} = 100 °C	-	240	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α

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Table 5. Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

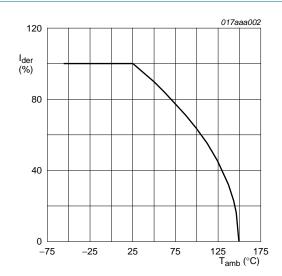
			-		
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = 25 ^{\circ}C$	[2] _	250	mW
			[1] -	300	mW
		T _{sp} = 25 °C	-	770	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	rain diode				
Is	source current	T _{amb} = 25 °C	[1] -	310	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

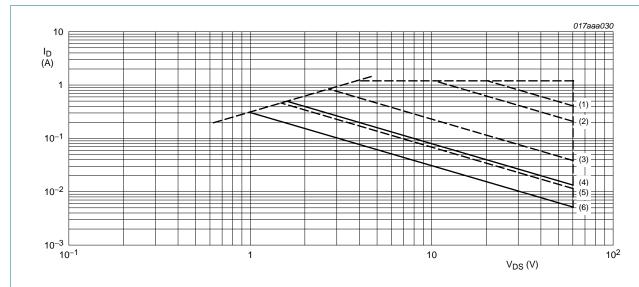
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

60 V, 310 mA N-channel Trench MOSFET



I_{DM} = single pulse

- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25 \, ^{\circ}C$
- (5) $t_p = 100 \text{ ms}$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

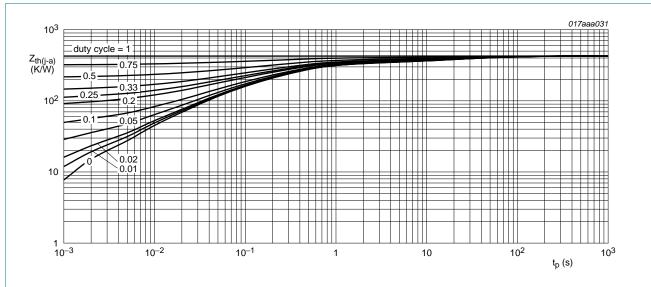
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	440	510	K/W
			[2]	360	415	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	160	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

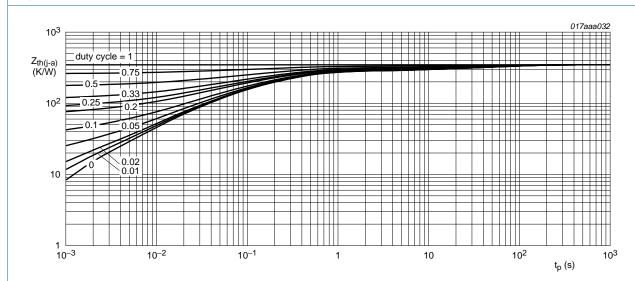
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 310 mA N-channel Trench MOSFET

7. Characteristics

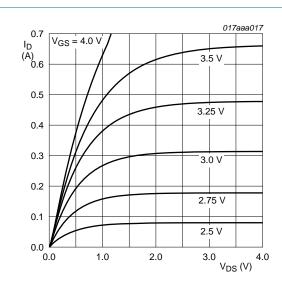
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.75	2.4	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
Doon	drain-source on-state resistance		<u>[1]</u>			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	400	-	mS
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.6	8.0	nC
Q_{GS}	gate-source charge	V _{DS} = 30 V; - V _{GS} = 4.5 V	-	0.2	-	nC
Q_{GD}	gate-drain charge	VGS = 4.5 V	-	0.2	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	30	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	рF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DD} = 50 \text{ V};$	-	3	6	ns
t _r	rise time	$R_L = 250 \Omega;$ - V _{GS} = 10 V;	-	4	-	ns
t _{d(off)}	turn-off delay time	$R_{G} = 6 \Omega$	-	10	20	ns
t _f	fall time	-	-	5	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

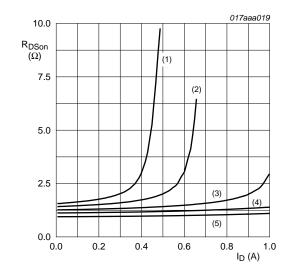
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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 $T_{amb} = 25 \, ^{\circ}C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_{amb} = 25 °C

(1) $V_{GS} = 3.25 \text{ V}$

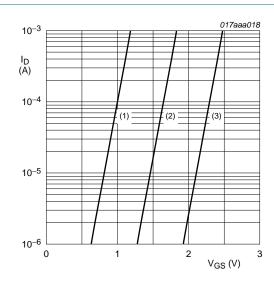
(2) $V_{GS} = 3.5 \text{ V}$

(3) $V_{GS} = 4 V$

(4) $V_{GS} = 5 \text{ V}$

(5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



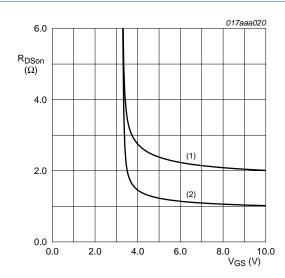
 T_{amb} = 25 °C; V_{DS} = 5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



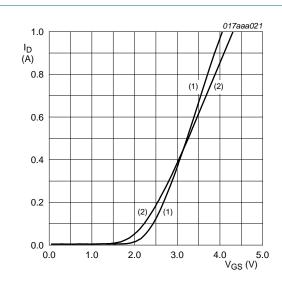
 $I_D = 500 \text{ mA}$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

60 V, 310 mA N-channel Trench MOSFET

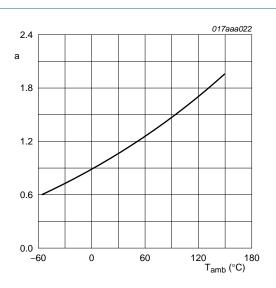


$$V_{DS} > I_D \times R_{DSon}$$

(1)
$$T_{amb} = 25 \, ^{\circ}C$$

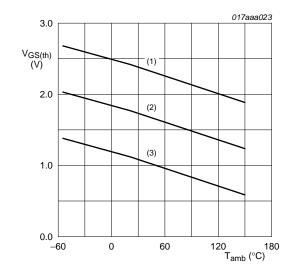
(2)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

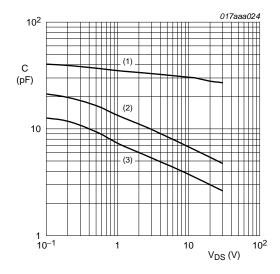
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

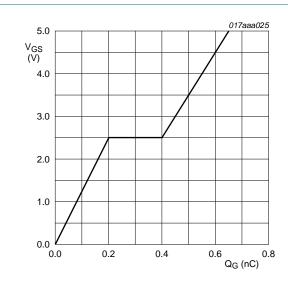


 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

60 V, 310 mA N-channel Trench MOSFET



 I_D = 300 mA; V_{DS} = 30 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

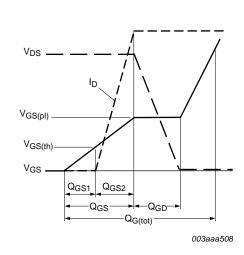
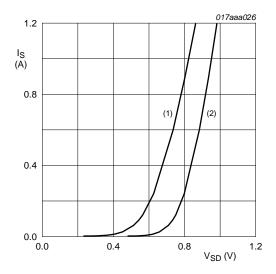


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

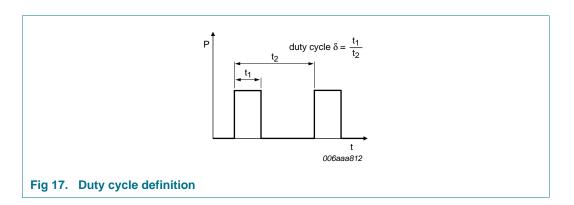
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 310 mA N-channel Trench MOSFET

9. Package outline

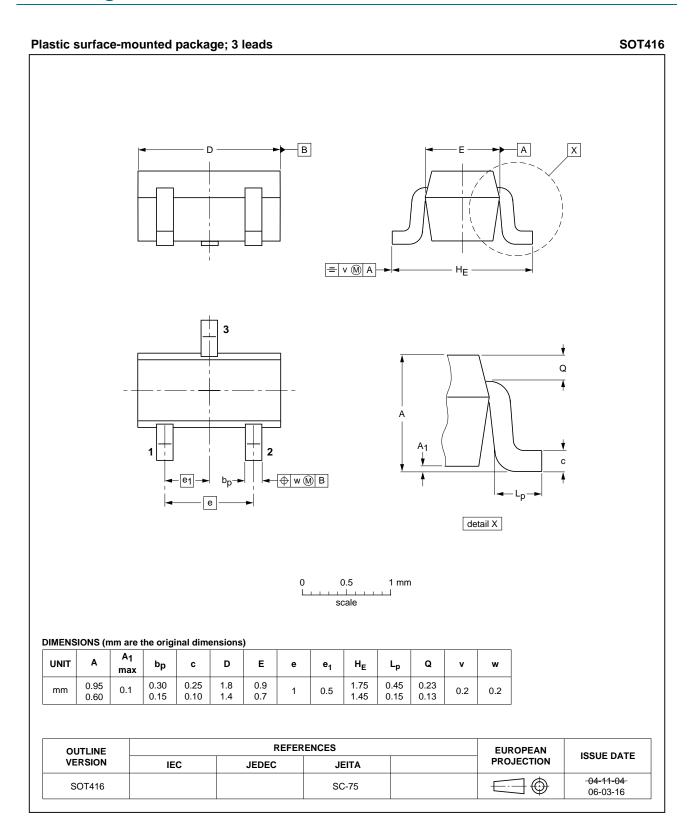


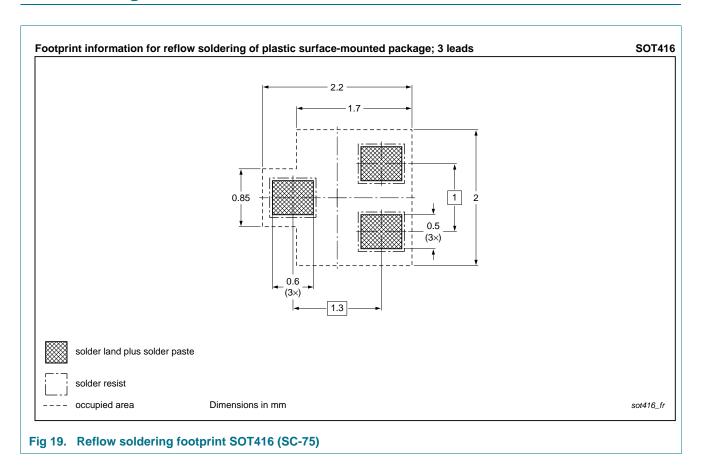
Fig 18. Package outline SOT416 (SC-75)

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60 V, 310 mA N-channel Trench MOSFET

10. Soldering



60 V, 310 mA N-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002PT v.1	20100702	Product data sheet	-	-

60 V, 310 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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60 V, 310 mA N-channel Trench MOSFET

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